國立中山大學102學年度第一學期資工系數位系統期末考試

學號: 姓名:

一、選擇與是非題(每題3分,12分)

- () 1. How many address lines are required in a 1G×32 RAM? ①9 ②30 ③32 ④35
- () 2. The clock inputs of all flip-flops in binary ripple counter receive a common clock.
- () 3. SRAM is the non-volatile memory.
- () 4. Programmable read-only memory (PROM) has fixed AND array and programmable OR array.

二、問答題(90分)

1. Derive the following terms for the sequential circuit shown in Fig. 1.

- (1) Input (Excitation) equations (4%)
 (2) State equations (6%)
 (3) State table (Table 1) (4%)
 (4) State diagram (4%)
- 2. Design a sequential circuit with two JK flip-flops A and B and two inputs E and F. If E=0, the circuit remains in the same state regardless of the value of F. When E=1 and F=1, the circuit go through the state transitions from 00 to 01, to 10, to 11, back to 00, and repeats. When E=1 and F=0, the circuit goes through the state transitions from 00 to 11, to 10, to 01, back to 00, and repeats.
 - (1) Complete the state table and JK flip-flop input as shown in Table 2. (8%)
 - (2) Derive the simplified flip-flop input (excitation) equations using the K-map. (12%)
 - (3) Draw the logic diagram with JK flip-flops as shown in Fig. 2. (6%)
- **3.** Design a counter with *T* flip-flops that goes through the following binary repeated sequence: 0, 1, 3, 7, 6, 4. Assume that binary states 010 and 101 are considered as don't care conditions.
 - (1) Complete the state table as shown in Table 3. (6%)
 - (2) Derive the simplified flip-flop input (excitation) equations. (6%)
 - (3) The counter may not operate properly if the unused states are treated as don't care condition. Find a way to correct the design and please explain your way. (4%)
- 4. Using an 8 × 2 ROM shown in Fig. 3 and a 3 × 4 × 2 PLA shown in Fig. 4, implement the truth table shown in Table 4. (6%) (8%)
- **5.** Please answer the following problems.
 - (1) Explain the operations of the 4-bit universal shift register shown in Fig. 5 and complete the function table shown in Table 5. (6%)
 - (2) Explain the read and write operations of the 4 × 4 RAM and the memory cell as shown in Fig. 6(a) and 6(b), respectively. (10%)





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